



Dual P-Channel 2.5-V (G-S) MOSFET

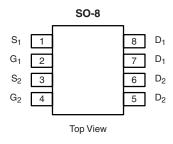
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
- 20	0.06 at V _{GS} = - 4.5 V	- 4.7		
	0.10 at V _{GS} = - 2.5 V	- 3.7		

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Compliant to RoHS Directive 2002/95/EC

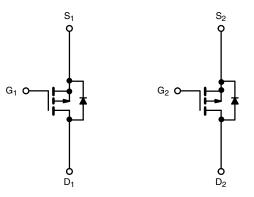






Ordering Information: Si9933BDY-T1-E3 (Lead (Pb)-free)

Si9933BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 20		V
Gate-Source Voltage		V _{GS}	± 12		
Continuous Dunis Comment /T 150 °C\d	T _A = 25 °C	I _D	- 4.7	- 3.6	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 3.8	- 2.8	
Pulsed Drain Current		I _{DM}	- 20		A
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.7	- 0.9	1
Maximum Power Dissipation ^a	T _A = 25 °C	- P _D	2.0	1.1	W
	T _A = 70 °C		1.3	0.7	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manipana lugation to Ambient	t ≤ 10 s	- R _{thJA}	55	62.5	°C/W
Maximum Junction-to-Ambient ^a	Steady State		90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	33	40	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

For SPICE model information via the Worldwide Web: www.vishay.com/www/product/spice.htm

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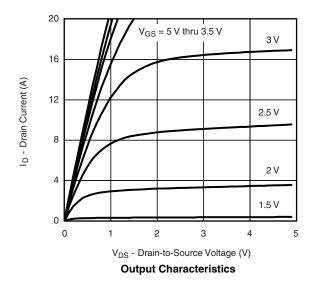
Parameter	Symbol	bol Test Conditions		Тур.	Max.	Unit
Static				•		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$ - 0.6		- 1.4	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V	- 1		- 1	
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 5	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			Α
Drain-Source On-State Resistance ^a	В	V _{GS} = - 4.5 V, I _D = - 4.7 A		0.048	0.06	0
	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 1 A		0.08	0.10	Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 4.7 A		11		S
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.7 A, V _{GS} = 0 V		- 0.75	- 1.2	V
Dynamic ^b				•		
Total Gate Charge	Q_g			6	9	
Gate-Source Charge	Q_{gs}	Q_{gs} $V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -4.7 \text{ A}$		1.4		nC
Gate-Drain Charge	Q_{gd}			1.9		
Gate Resistance	R_g	f = 1 MHz		9.5		Ω
Turn-On Delay Time	t _{d(on)}			22	35	
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		35	55	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -1 \text{ A, } V_{GEN} = -4.5 \text{ V, } R_g = 6 \Omega$		45	70	ns
Fall Time	t _f			25	40	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.7 A, dl/dt = 100 A/μs		25	50	

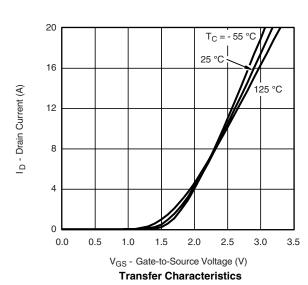
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



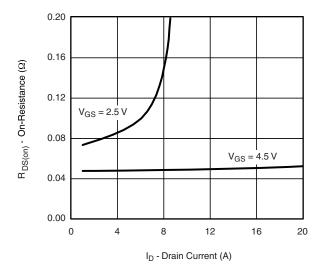




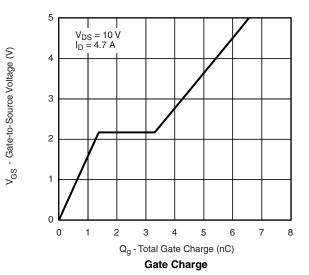


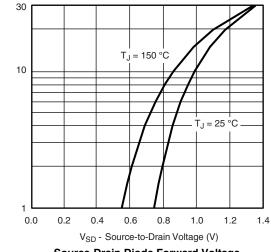


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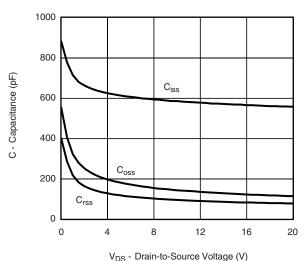


On-Resistance vs. Drain Current

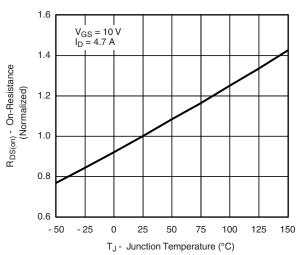




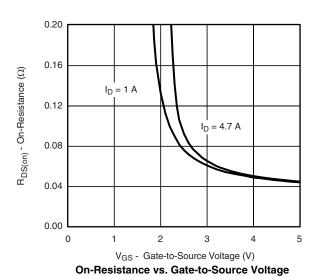
Source-Drain Diode Forward Voltage







On-Resistance vs. Junction Temperature

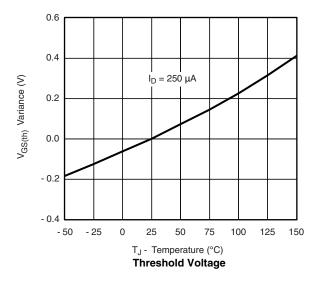


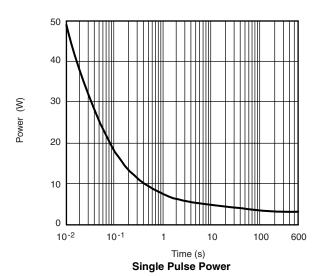
I_S - Source Current (A)

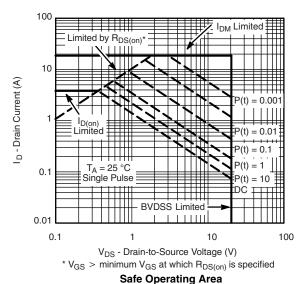
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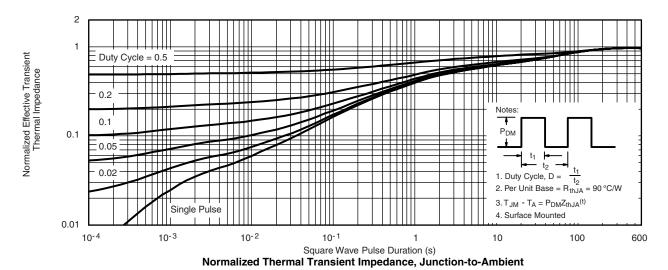
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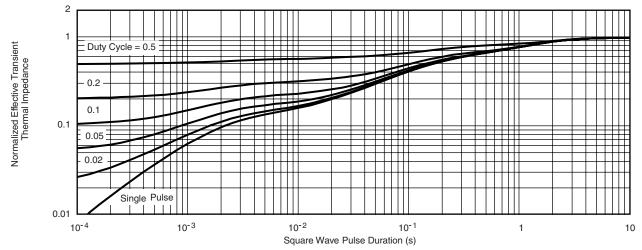








TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72748.



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